



P-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

| BV _{DSS} / BV _{DGS} | R _{DS(ON)} (max) | I _{D(ON)} (min) | Order Number / Package |
|---------------------------------------|---------------------------|--------------------------|------------------------|
| | | | TO-92 |
| -30V | 2.5Ω | -1.5A | VP0300L |

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Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- Integral Source-Drain diode
- High input impedance and high gain
- Complementary N- and P-channel devices

Advanced DMOS Technology

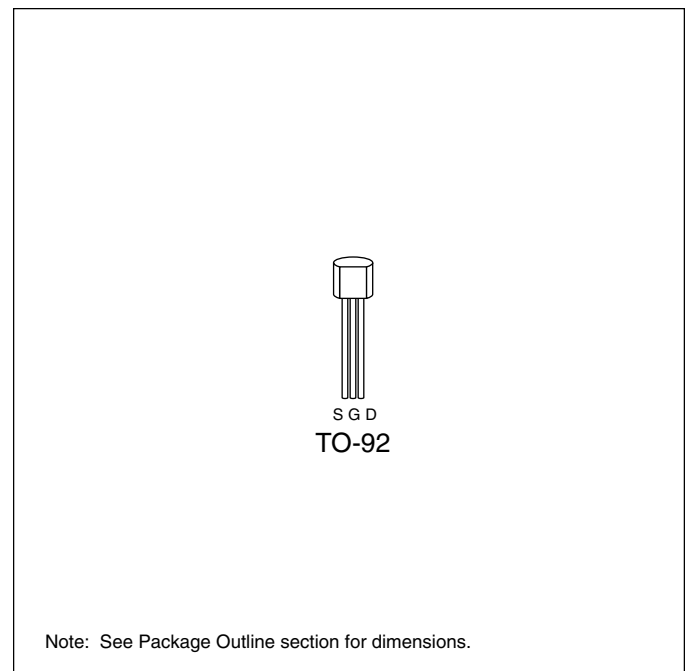
These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

Package Options



Absolute Maximum Ratings

| | |
|-----------------------------------|-------------------|
| Drain-to-Source Voltage | BV _{DSS} |
| Drain-to-Gate Voltage | BV _{DGS} |
| Gate-to-Source Voltage | ± 20V |
| Operating and Storage Temperature | -55°C to +150°C |
| Soldering Temperature* | 300°C |

* Distance of 1.6 mm from case for 10 seconds.

Thermal Characteristics

| Package | I_D (continuous)* | I_D (pulsed) | Power Dissipation $T_C = 25^\circ\text{C}$ | θ_{ja} $^\circ\text{C/W}$ | θ_{jc} $^\circ\text{C/W}$ |
|---------|---------------------|----------------|---|-------------------------------------|-------------------------------------|
| TO-92 | -0.32A | -0.87A | 1.0W | 170 | 125 |

* I_D (continuous) is limited by max rated T_j .

- OBSOLETE -

Electrical Characteristics (@ 25°C unless otherwise specified)

| Symbol | Parameter | Min | Typ | Max | Unit | Conditions |
|--------------|--|------|------|------|------------|---|
| BV_{DSS} | Drain-to-Source Breakdown Voltage | -30 | | | V | $V_{GS} = 0V, I_D = -10\mu A$ |
| $V_{GS(th)}$ | Gate Threshold Voltage | -1.0 | -1.8 | -4.5 | V | $V_{GS} = V_{DS}, I_D = -1mA$ |
| I_{GSS} | Gate Body Leakage | | | -100 | nA | $V_{GS} = \pm 30V, V_{DS} = 0V$ |
| I_{DSS} | Zero Gate Voltage Drain Current | | | -10 | μA | $V_{GS} = 0V, V_{DS} = -25V$ |
| | | | | -500 | | $V_{GS} = 0V, V_{DS} = -25V$ $T_A = 125^\circ\text{C}$ |
| $I_{D(ON)}$ | ON-State Drain Current | -1.5 | -1.7 | | A | $V_{GS} = -12V, V_{DS} = -10V$ |
| $R_{DS(ON)}$ | Static Drain-to-Source ON-State Resistance | | | 2.5 | Ω | $V_{GS} = -12V, I_D = -1A$ |
| G_{FS} | Forward Transconductance | 200 | | | $m\bar{S}$ | $V_{DS} = -10V, I_D = -0.5A$ |
| C_{ISS} | Input Capacitance | | | 150 | pF | $V_{GS} = 0V, V_{DS} = -15V$ $f = 1MHz$ |
| C_{OSS} | Common Source Output Capacitance | | | 120 | | |
| C_{RSS} | Reverse Transfer Capacitance | | | 60 | | |
| $t_{(ON)}$ | Turn-ON Time | | | 30 | ns | $V_{DD} = -25V, I_D = -1A$ $R_{GEN} = 25\Omega$ |
| $t_{(OFF)}$ | Turn-OFF Time | | | 30 | | |
| V_{SD} | Diode Forward Voltage Drop | | -1.2 | | V | $V_{GS} = 0V, I_{SD} = -1.5A$ |

Notes

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

